Dual N-Channel 20-V (D-S) MOSFET, Common Drain

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.026 at V_{GS} = 4.5 V	8.5
	0.030 at V_{GS} = 2.5 V	8
	0.036 at V_{GS} = 1.8 V	7

FEATURES

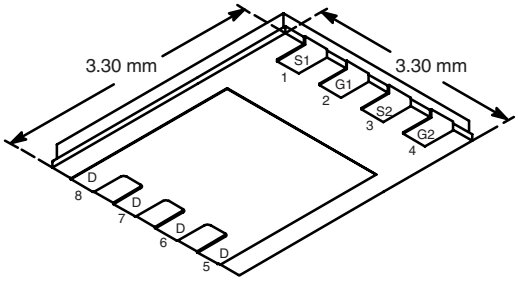
- **Halogen-free Option Available**
- TrenchFET® Power MOSFET: 1.8 V Rated
- New PowerPak® Package
  - Low Thermal Resistance, R_{thJC}
  - Low 1.07 mm Profile
- 3000 V ESD Protection

Pb-free
RoHS COMPLIANT

APPLICATIONS

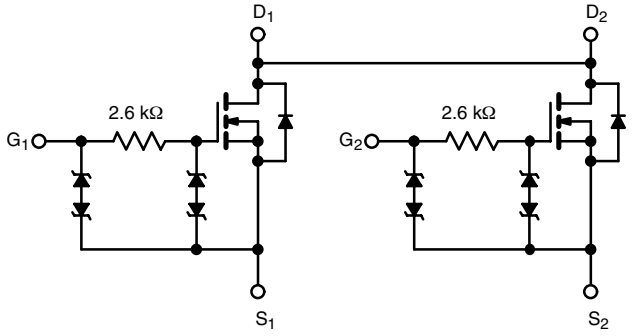
- Protection Switch for 1-2 Li-ion Batteries

PowerPAK 1212-8



Bottom View

Ordering Information: Si7900AEDN-T1-E3 (Lead (Pb)-free)
Si7900AEDN-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel N-Channel

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	8.5	6	A
	T_A = 85 °C		6.4	4.3	
Pulsed Drain Current		I_{DM}	30		
Continuous Source Current (Diode Conduction)[a]		I_S	2.9	1.4	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	3.1	1.5	W
	T_A = 85 °C		1.6	0.79	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	32	40	°C/W
	Steady State		65	82	
Maximum Junction-to-Case	Steady State	R_{thJC}	2.2	2.8	

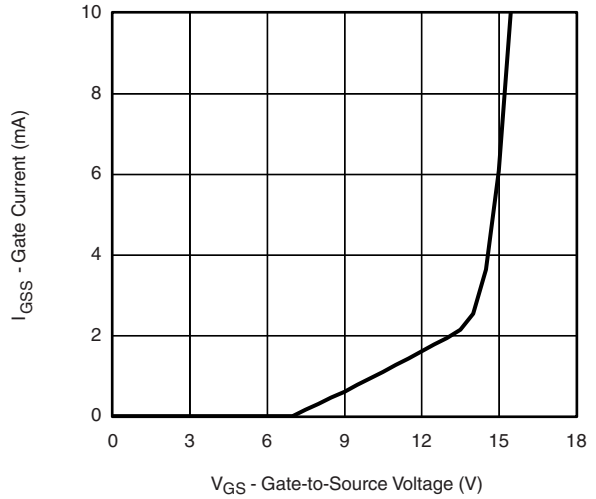
Notes:
a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.40		0.9	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 4.5 V			± 1	µA
		V_{DS} = 0 V, V_{GS} = ± 12 V			± 10	mA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 85 °C			20	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V	20			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 8.5 A		0.020	0.026	Ω
		V_{GS} = 2.5 V, I_D = 8 A		0.022	0.030	
		V_{GS} = 1.8 V, I_D = 7 A		0.026	0.036	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 8.5 A		25		S
Diode Forward Voltage[a]	V_{SD}	I_S = 2.9 A, V_{GS} = 0 V		0.65	1.1	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 6.5 A		10.5	16	nC
Gate-Source Charge	Q_{gs}			1.9		
Gate-Drain Charge	Q_{gd}			1.8		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 10 Ω I_D ≅ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		0.85	1.25	ns
Rise Time	t_r			1.3	2.0	
Turn-Off Delay Time	$t_{d(off)}$			8.6	13	
Fall Time	t_f			4.2	6.5	

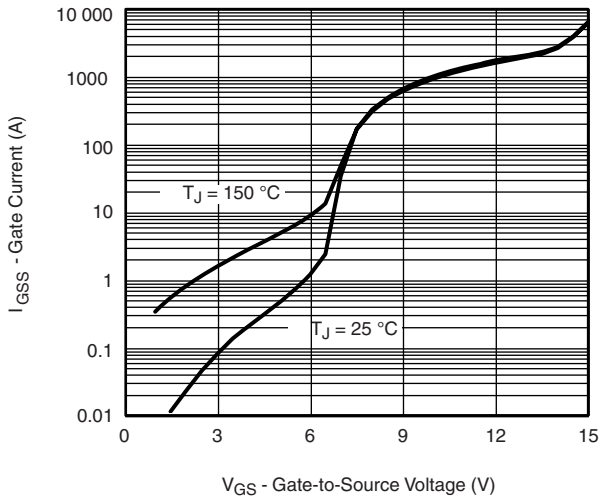
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

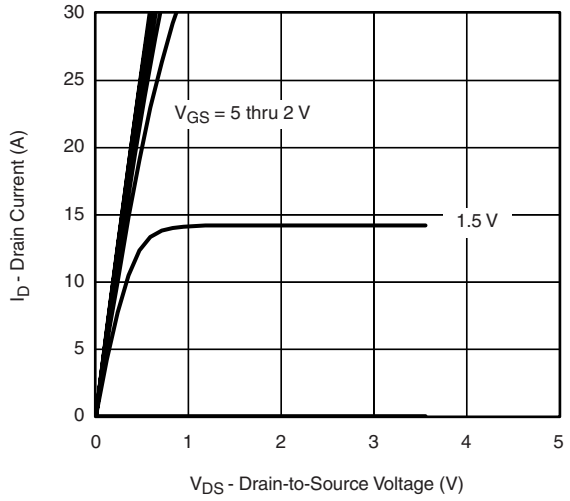


Gate-Current vs. Gate-Source Voltage

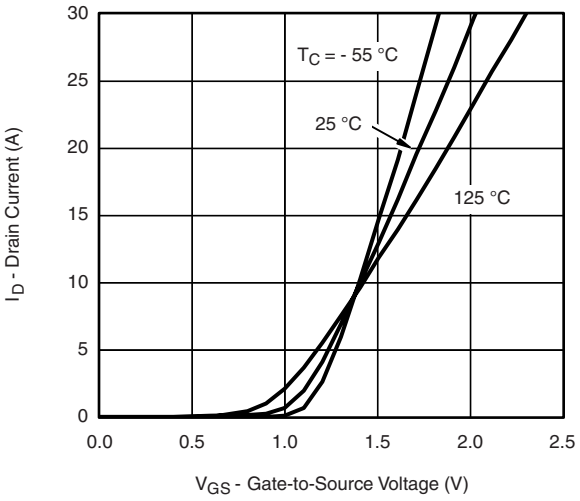


Gate Current vs. Gate-Source Voltage

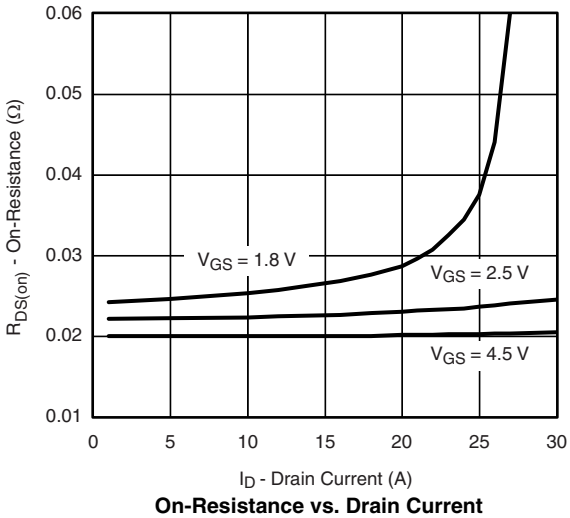
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



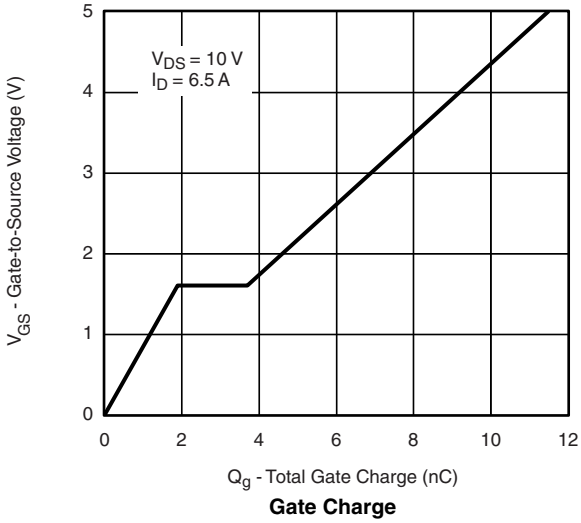
Output Characteristics



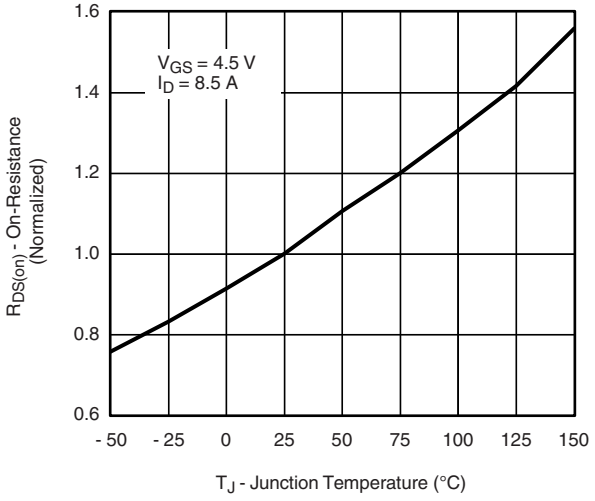
Transfer Characteristics



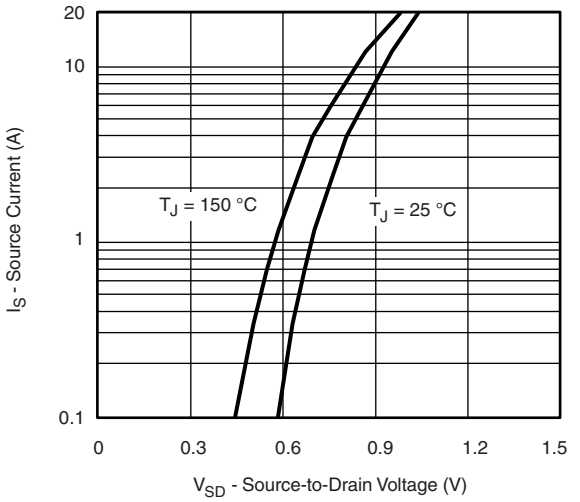
On-Resistance vs. Drain Current



Gate Charge

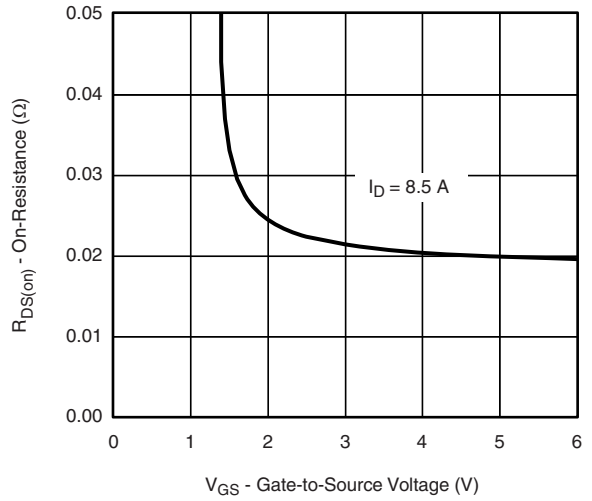


On-Resistance vs. Junction Temperature

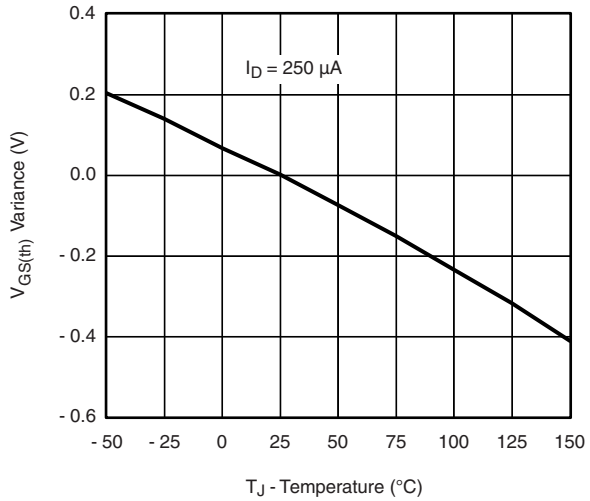


Source-Drain Diode Forward Voltage

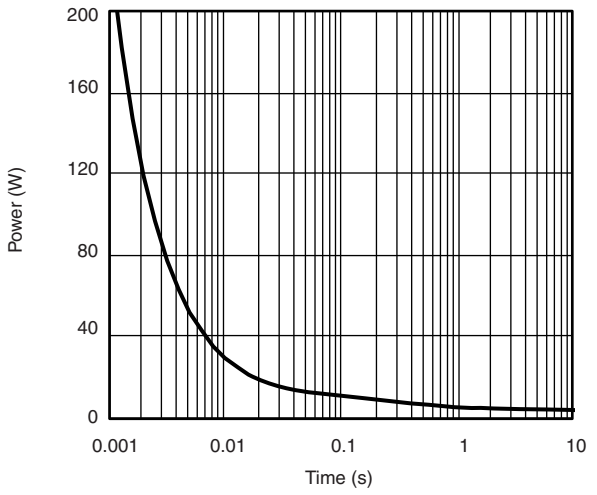
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



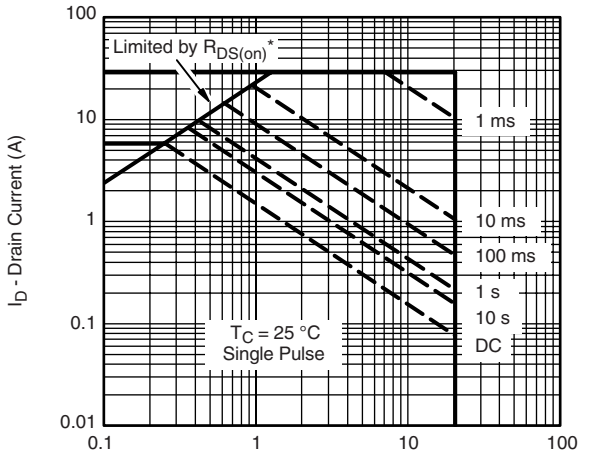
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

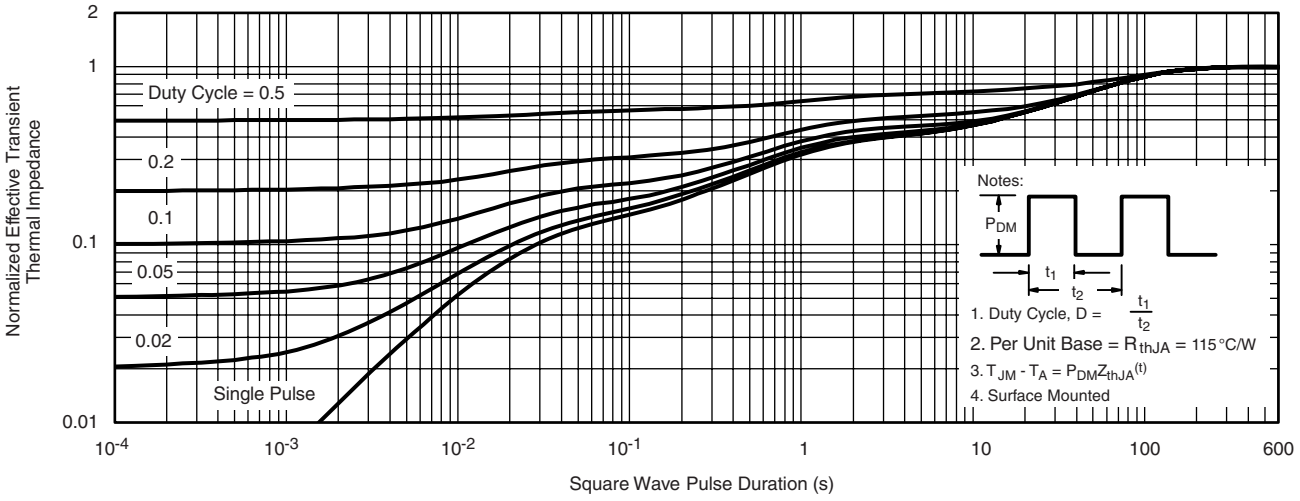


Single Pulse Power, Junction-to-Ambient



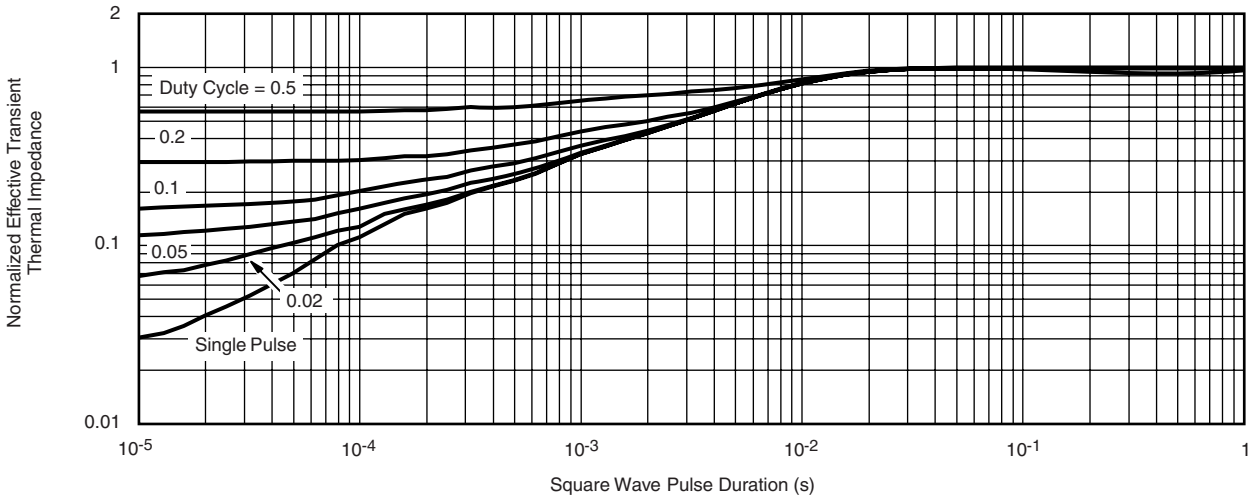
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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